



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

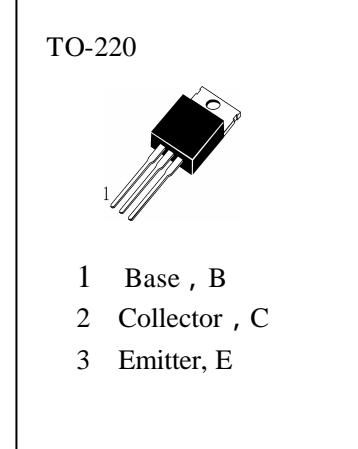
HB834

APPLICATIONS

Low Frequency Power Amplifier.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_C —Collector Dissipation ($T_c=25^\circ C$)	30W
P_C —Collector Dissipation ($T_a=25^\circ C$)	1.5W
V_{CBO} —Collector-Base Voltage.....	-60V
V_{CEO} —Collector-Emitter Voltage.....	-60V
V_{EBO} —Emitter-Base Voltage.....	-7V
I_C —Collector Current.....	-3A
I_B —Base Current.....	-0.5A



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage	-60			V	$I_C=-50mA, I_B=0$
ICBO	Collector Cut-off Current			-100	μA	$V_{CB}=-60V, I_E=0$
IEBO	Emitter Cut-off Current			-100	μA	$V_{EB}=-7V, I_C=0$
HFE (1)	DC Current Gain	60		200		$V_{CE}=-5V, I_C=-0.5A$
HFE (2)	DC Current Gain	20				$V_{CE}=-5V, I_C=-3A$
VCE(sat)	Collector- Emitter Saturation Voltage		-0.5	-1	V	$I_C=-3A, I_B=-0.3A$
VBE(on)	Base-Emitter On Voltage		-0.7	-1	V	$V_{CE}=-5V, I_C=-0.5A$
f _t	Current Gain-Bandwidth Product		9		MHz	$V_{CE}=-5V, I_C=-0.5A,$
Cob	Output Capacitance		150		pF	$V_{CB}=-10V, I_E=0, f=1MHz$
ton	Turn-On Time		0.4		μs	
t _{STG}	Storage Time		1.7		μs	
t _F	Fall Time		0.5		μs	
						$I_{B1} = -I_{B2} = -0.2A$ $V_{CC} = 30V$

h_{FE} Classification

O

Y

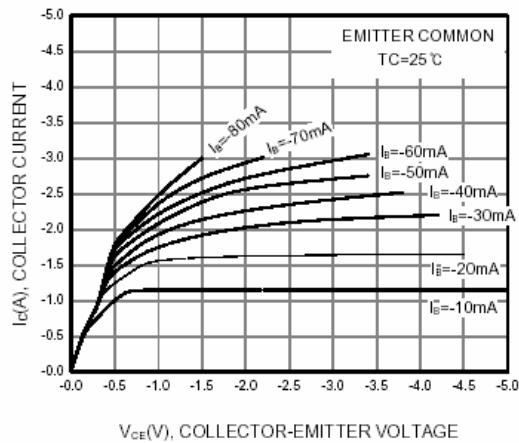
60—120

100—200



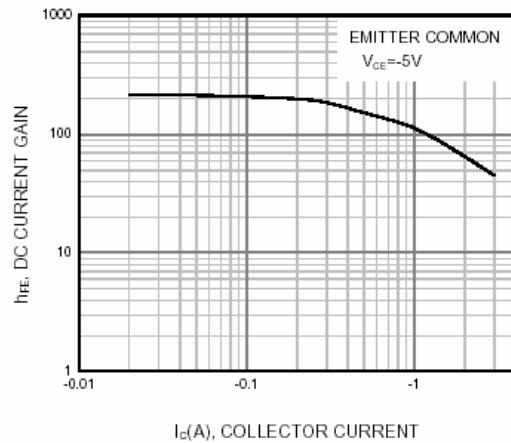
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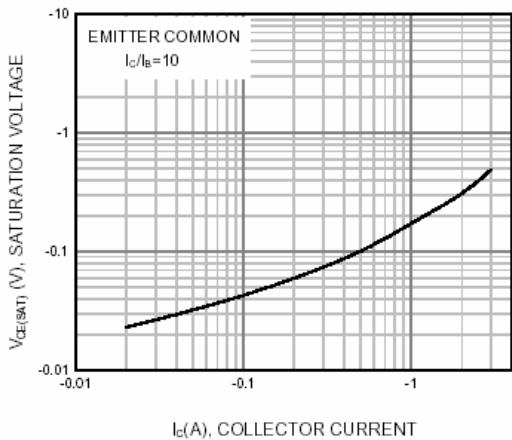
V_{CE} (V), COLLECTOR-EMITTER VOLTAGE

Figure 1. Static Characteristic



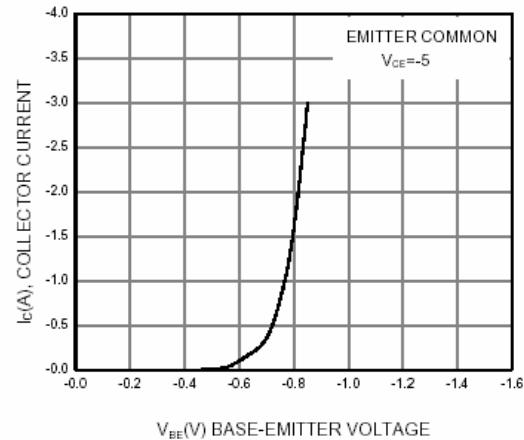
I_C (A), COLLECTOR CURRENT

Figure 2. DC current Gain



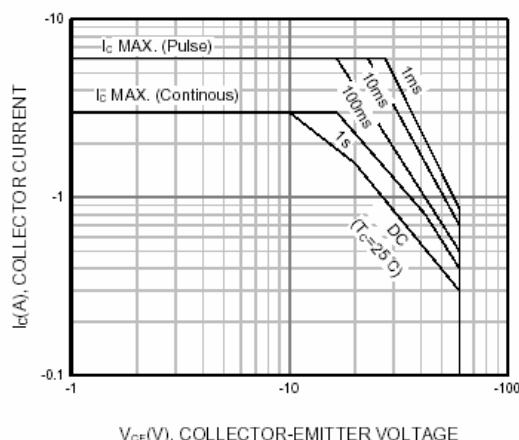
I_C (A), COLLECTOR CURRENT

Figure 3. Collector-Emitter Saturation Voltage



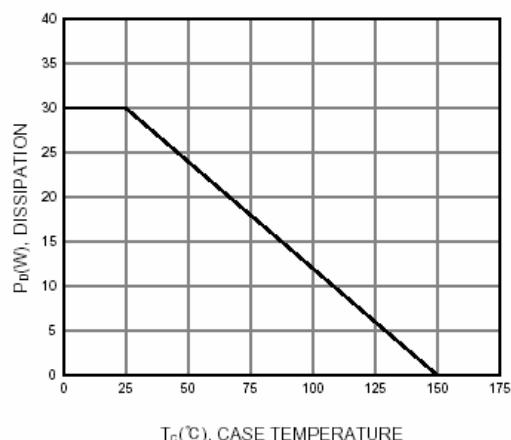
V_{BE} (V) BASE-EMITTER VOLTAGE

Figure 4. Base-Emitter On Voltage



V_{CE} (V), COLLECTOR-EMITTER VOLTAGE

Figure 5. Safe Operating Area



T_C (°C), CASE TEMPERATURE

Figure 6. Power Derating